

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	59329	((reactive near ion near etch\$3) RIE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 12:59
S2	489	S1 same silica and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:03
S3	17	S1 same silica and (silicon near wafer) and plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:04
S4	3292	S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:05
S5	484	S4 and plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:05
S6	530	S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3) same (silicon semiconductor) near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:08
S7	50	S6 and plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:05
S8	15	S6 same plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:08
S9	560	S1 same (silica (silicon near \$3oxide)) near3 (film layer coat\$3 deposit\$9) same (silicon semiconductor) near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:12

S10	15	S9 same plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:27
S11	0	S10 not S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:09
S12	1643	plasma near9 (film layer coat\$3 deposit\$9) same (silica (silicon near \$3oxide)) same (silicon semiconductor) near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:13
S13	47	RF near9 plasma near9 (film layer coat\$3 deposit\$9) same (silica (silicon near \$3oxide)) same (silicon semiconductor) near3 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:14
S14	1	S13 and RF near9 (power source) near9 connect\$3 near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:17
S15	0	RF near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer electrode) same (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone polymer organopolysiloxane polyorganosiloxane) near3 (deposit layer film coat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:20
S16	29	RF near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone polymer organopolysiloxane polyorganosiloxane) near3 (deposit layer film coat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:26
S17	139	(RF (radio frequency)) near9 (power source) near9 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone organopolysiloxane polyorganosiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:28

S18	52	S17 and plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:29
S19	53	(RF (radio frequency)) near9 (power source) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer electrode) and (treat\$9 harden\$9 cross\$1link\$3) near9 (silicone organopolysiloxane polyorganosiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:37
S20	24	S19 and plasma same (hydrogen "H.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:29
S21	13	(RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same (treat\$9 harden\$9 cross\$1link\$3) near9 (silicon\$3 \$5organopolysiloxane polyorganosiloxane \$5organosiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:45
S22	32	(RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same (treat\$9 harden\$9 coat\$3 deposit\$9 layer film cross\$1link\$3) near9 (silicon\$3 \$5organopolysiloxane polyorganosiloxane \$5organosiloxane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:39
S23	15	(RF (radio frequency)) near9 (power source generat\$5) near9 connect\$9 near9 ((substrate near3 (silicon semiconductor)) wafer) and plasma near9 (hydrogen "H. sub.2") same insulat\$5 near3 (deposit\$9 coat\$3 film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 13:46
S24	13	(RF plasma) near9 (power source) near9 connect\$3 near3 ((substrate near3 (silicon semiconductor)) wafer) same (post\$1treat\$9 treat\$9 harden\$9 cross\$1link\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:30

S25	23	(RF plasma) near9 (power source) near9 connect\$3 near3 (((substrate support) near3 (silicon semiconductor electrode)) wafer) same (post\$1treat\$9 treat\$9 harden\$9 cross\$1link\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:17
S26	2	"07235524"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 14:36
S27	1247	(RF near9 high near frequency near9 plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:18
S28	232	(RF near9 high adj frequency near9 plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:18
S29	91	(RF near9 high adj frequency near plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:18
S30	10	(RF near high adj frequency near plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:57
S31	14411	((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (silica (silicon near \$3oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:59
S32	1658	S31 same (chamber apparatus)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 15:58
S33	830	((chemical near vapo\$1r near deposition) Cvd) near9 plasma near9 (chamber apparatus) same (silica (silicon near \$3oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:00
S34	496	((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) same (silica (silicon near \$3oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:00

S35	240	((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 (silica (silicon near \$3oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:00
S36	28	((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 (silane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:02
S37	1	((chemical near vapo\$1r near deposition) Cvd) near plasma near9 (chamber apparatus) near9 fig\$4 same (silane disilane methylsilane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:04
S38	1	((chemical near vapo\$1r near deposition) Cvd) near plasma near9 fig\$4 same (silane disilane methylsilane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:04
S39	19	((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (silane disilane methylsilane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:05
S40	3	((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (chamber apparatus) same (silane disilane methylsilane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:06
S41	24	((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (chamber apparatus) and (silane disilane methylsilane organosilane) same oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:08
S42	127	((chemical near vapo\$1r near deposition) Cvd) near3 plasma same fig\$4 same (device chamber apparatus) and (silane disilane methylsilane organosilane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:12
S43	202	((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (power source) near9 connect\$5 near9 (substrate support)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:14

S44	64	((chemical near vapo\$1r near deposition) Cvd) near9 plasma same (power source) near3 connect\$5 near3 (substrate support)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:07
S45	4	"10004062"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 16:17
S46	126	"5314724"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:07
S47	2	"5314724".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 18:07